	Тур е	L #	Hits	Search Text	DBs	Time Stamp	mm en	Err or Def ini tio n	Er ro
1	BRS	L1	5191	variable near2 impedance\$	ILI C D A T	2006/02/ 02 15:46			
2	BRS	L2	9228	(variable or adjust\$) near2 impedance\$	III C D A T	2006/02/ 02 18:31			
3	BRS	L3	12338	equal near2 potential\$	ILIC DATE	2006/02/ 02 15:54	1		
4	BRS	L4	18250	(equal or even) near2 potential\$	ILIC DATE	2006/02/ 02 15:54	1		
5	BRS	L5	225	2 and 3	USPAT	2006/02/ 02 15:56	1	:	
6	BRS	L6	25815 7	resistor\$	USPAT	2006/02/ 02 18:32			
7	BRS	ь7	28159 3	transistor\$	USPAT	2006/02/ 02 18:32			
8	BRS	L8	139	5 and 6 and 7	III C D A T	2006/02/ 02 15:57	•	_	
9	BRS	L9	30658	(variable or adjust\$) near2 gain	USPAT	2006/02/ 02 18:32			
10	BRS	L10	24717	agc	USPAT	2006/02/ 02 16:16			
11	BRS	L11	669	2 and 6 and 7 and 9	USPAT	2006/02/ 02 16:16			
12	BRS	L12	108	11 and 10	USPAT	2006/02/ 02 17:29			

	Тур	L #	Hits	Search Text	DBs	Time Stamp	mm en	Err or Def ini tio	Er
13	BRS	L13	ì	resistor\$ near2 series near2 (transistor\$ or (variable adj impedance))	ILIC DATE	2006/02/ 02 18:33			
14	BRS	L14	33	11 and 13	יויאטאוו	2006/02/ 02 16:19			
15	BRS	L15	675	330/254.ccls.	1110001	2006/02/ 02 18:21			
16	BRS	L16	329	330/278.ccls.	USPAT	2006/02/ 02 18:21			
17	BRS	L17	251	327/359.ccls.	USPAT	2006/02/ 02 18:25			,
18	BRS	L18	379	327/356.ccls.	USPAT	2006/02/ 02 18:25			
19	BRS	L19	11081	(variable or adjustable) near2 impedance\$	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/ 02 18:32			
20	BRS	L20	44333 2	resistor\$		2006/02/ 02 18:32			
21	BRS	L21	52840 6	transistor\$	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/ 02 18:32			

	Тур е	L #	Hits	Search Text	DBs	Time Stamp	mm en	Err or Def ini tio	Er
22	BRS	L22	18816	(variable or adjustable)	(P. DUV + I DUV +	2006/02/ 02 18:33			
23	BRS	L23		resistor\$ near2 series near2 (transistor\$ or	IN' D( ) • I D( ) •	2006/02/ 02 18:33			
24	BRS	L24	ソ	19 and 20 and 21 and 22	IP. D() • . I D() •	2006/02/ 02 18:34	•		
25	BRS	L25	195	19 and 20 and 21 and 22	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/ 02 18:34			